

	Ref #	Search Text
74	S74	"LDMOS" (lateral near3 diffus\$3 near5 (transistor gate electrode)) "DEMOS" (drain near3 extend\$3 near4 (transistor gate electrode))
75	S75	"CMOS" "PMOS" "NMOS" ("P" near3 (metal adj3 semiconductor)) ("N" near3 (metal adj3 semiconductor))
76	S76	("20020009790" "20020030238" "20020089790" "20030141559" "20040046226" "20040180485" "20040238913" "6160289" "6384643" "6400126" "6642697" "6855985"). PN.
77	S77	S74 same S75
78	S78	@ad<= "20031103" or @rlad<= "20031103"
79	S79	S77 and S78
80	S80	("P" near3 body) same ("P" near3 well) ("N" near3 well)
81	S81	("P" near3 body) same ((P" near3 well) ("N" near3 well) well)
82	S82	S81 and S79

	DBs
74	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
75	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
76	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
77	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
78	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
79	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
80	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
81	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
82	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB

	L #	Search Text
1	L1	(438/202).CCLS.
2	L2	(438/204).CCLS.
3	L3	(438/223).CCLS.
4	L4	(438/224).CCLS.
5	L5	(438/227).CCLS.
6	L7	(438/278).CCLS.
7	L8	(438/527).CCLS.
8	L6	(438/275).CCLS.

	DBs
1	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
2	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
5	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
7	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
8	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB